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ON Semiconductor®

Energy Efficient Innovations

Product Overview

FOD819: Phototransistor Optocouplers, High Speed, 4-Pin DIP

For complete documentation, see the data sheet.

The FOD819 consists of a gallium arsenide (GaAs) infra-red emitting diode, driving a high speed photo detector with integrated base-to-emitter resistor, R_{BE}, in a 4-pin dual-in-line package. It is designed to be an improved replacement to the popular FOD817 Series when higher speed performance is required in isolated data signal transmission.

Features

- High Speed Performance ~ 30kHz
- Current Transfer Ratio: 100% to 600%
- Minimum BV_{CEO} of 80V Guaranteed
- Safety and Regulatory Approvals:
- UL1577, 5,000 VAC_{RMS} for 1 Minute
- DIN EN/IEC60747-5-5, 850V Peak Working Insulation Voltage

Applications

- Digital Logic Inputs
- Microprocessor Inputs
- Power Supply Monitor
- Twisted Pair Line Receiver
- Telephone Line Receiver

Part Electrical Specifications

Product	Compliance	Status	Channels	CTR (Min) (%)	CTR (Max) (%)	CTR tested @ IF (mA)	$V_{CE(sat)}$ (Max) (V)	BV_{CEO} (Min) (V)	BV_{CBO} (Min) (V)	BV_{ECO} (Min) (V)	t_{on} (Max) (µs)	t_{off} (Max) (µs)	V_{ISO} (Min) (V)	T_{OPR} (Min) (°C)	T_{OPR} (Max) (°C)	Package Type
FOD819	Pb-free	Active	1	100	600	1.5	0.3	80		2	-	-	5000	-55	110	PDIP-4
FOD819S	Pb-free	Active	1	100	600	1.5	0.3	80		2	-	-	5000	-55	110	PDIP-4 GW
FOD819SD	Pb-free	Active	1	100	600	1.5	0.3	80		2	-	-	5000	-55	110	PDIP-4 GW

For more information please contact your local sales support at www.onsemi.com.

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